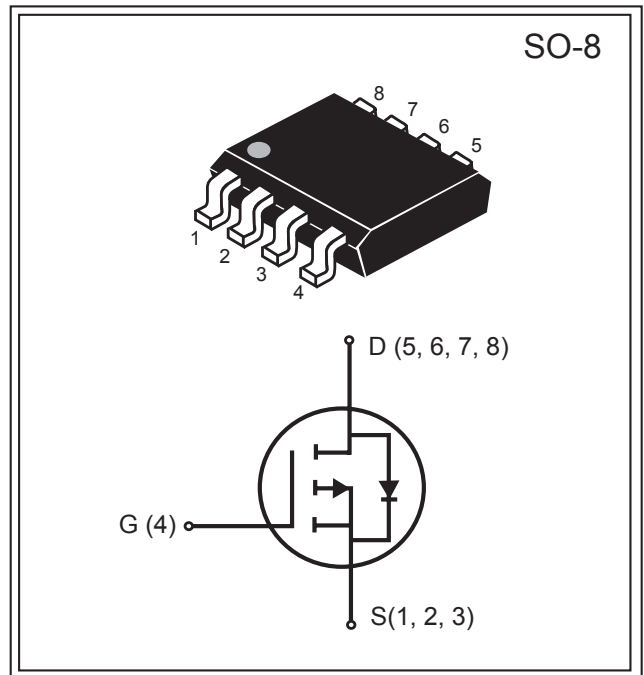




| Product Summary | | |
|---------------------|--------------------|------------------------------|
| V _{DS} (V) | I _D (A) | R _{DS(ON)} (mΩ) Max |
| - 30V | - 6.0A | 45 @V _{GS} = - 10V |
| | | 70 @V _{GS} = - 5V |
| | | 80 @V _{GS} = - 4.5V |



FEATURES

- ◆ Super high dense cell design for low R_{DS(ON)}.
- ◆ Rugged and reliable.
- ◆ Surface Mount package.

ABSOLUTE MAXIMUM RATINGS (T_A = 25°C unless otherwise noted)

| Parameter | Symbol | Limit | Unit |
|---|-----------------------------------|-------------|------|
| Drain-Source Voltage | V _{DS} | - 30 | V |
| Gate-Source Voltage | V _{GS} | ±25 | V |
| Drain Current-Continuous @ T _J = 125°C | I _D | - 6.0 | A |
| -Pulsed ^b | I _{DM} | - 30 | A |
| Drain-Source Diode Forward Current ^a | I _S | - 1.7 | A |
| Maximum Power Dissipation ^a | P _D | 2.5 | W |
| Operating Junction and Storage Temperature Range | T _J , T _{STG} | - 55 to 150 | °C |

THERMAL CHARACTERISTICS

| | | | |
|--|------------------|----|------|
| Thermal Resistance, Junction-to-Ambient ^a | R _{θJA} | 50 | °C/W |
|--|------------------|----|------|

South Sea Semiconductor reserves the right to make changes to improve reliability or manufacturability without advance notice.

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| P-Channel Electrical Characteristics (TA = 25°C unless otherwise noted) | | | | | | |
|---|---------------------|---|------|------------------|-------|------|
| Parameter | Symbol | Condition | Min | Typ ^c | Max | Unit |
| Drain-Source Breakdown Voltage | BV _{DSS} | V _{GS} =0V, I _D = - 250 μA | -30 | | | V |
| Zero Gate Voltage Drain Current | I _{DSS} | V _{DS} = - 24V, V _{GS} =0V | | | - 1 | μA |
| Gate-Body Leakage | I _{GSS} | V _{GS} = ±25V, V _{DS} =0V | | | ±100 | nA |
| Gate Threshold Voltage | V _{GS(th)} | V _{DS} =V _{GS} , I _D = - 250 μA | - 1 | - 1.9 | - 2.5 | V |
| Drain-Source On-State Resistance | R _{DS(ON)} | V _{GS} = - 10V, I _D = - 6.0A | | 38 | 45 | mΩ |
| | | V _{GS} = - 5V, I _D = - 4.0A | | 60 | 70 | |
| | | V _{GS} = - 4.5V, I _D = - 3.0A | | 70 | 80 | |
| On-State Drain Current | I _{D(ON)} | V _{DS} = - 5V, V _{GS} = - 10V | - 20 | | | A |
| Forward Transconductance | g _{FS} | V _{DS} = - 15V, I _D = - 5.3A | | 10 | | S |
| Input Capacitance | C _{ISS} | V _{DS} = - 15V | | 700 | 800 | pF |
| Output Capacitance | C _{OSS} | V _{GS} =0V | | 130 | | |
| Reverse Transfer Capacitance | C _{RSS} | f=1.0MHz | | 90 | | |
| Turn-On Delay Time | t _{D(ON)} | V _{DD} = - 15V, | | 10 | | ns |
| Rise Time | t _r | I _D = - 1A, | | 8 | | |
| Turn-Off Delay Time | t _{D(OFF)} | V _{GEN} = - 10V, | | 40 | | |
| Fall Time | t _f | R _{GEN} =6Ω, | | 30 | | |
| Total Gate Charge | Q _g | V _{DS} = -15V, I _D = -5.3A, V _{GS} = -10V | | 16 | 20 | nC |
| | | V _{DS} = -15V, I _D = -5.3A, V _{GS} = -4.5V | | 9 | | |
| Gate-Source Charge | Q _{gs} | V _{DS} = - 15V, I _D = - 6A, | | 3 | | |
| Gate-Drain Charge | Q _{gd} | V _{GS} = - 10V | | 3.5 | | |
| Diode Forward Voltage | V _{SD} | V _{GS} =0V, I _D = - 1.0A | | - 0.75 | - 1.2 | V |

Notes :

- a. Surface Mounted on FR4 Board, t ≤ 10 sec.
- b. Pulse Test : Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.
- c. Guaranteed by design, not subject to production testing.

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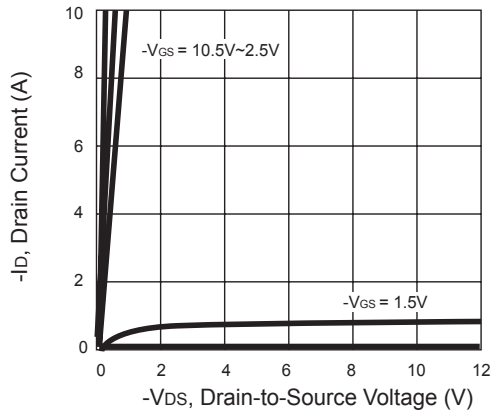


Figure 1. Output Characteristics

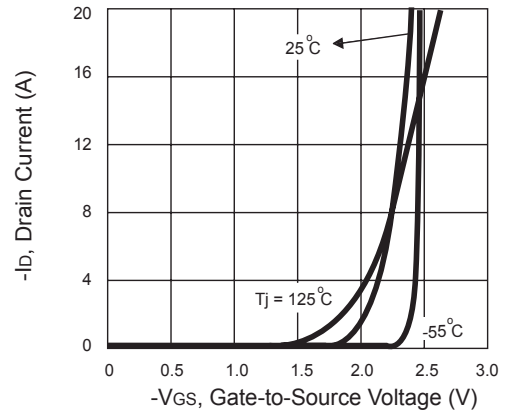


Figure 2. Transfer Characteristics

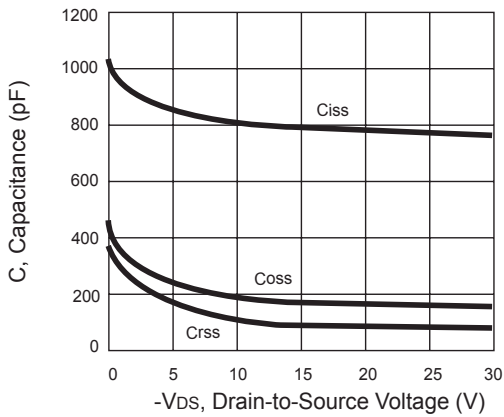


Figure 3. Capacitance

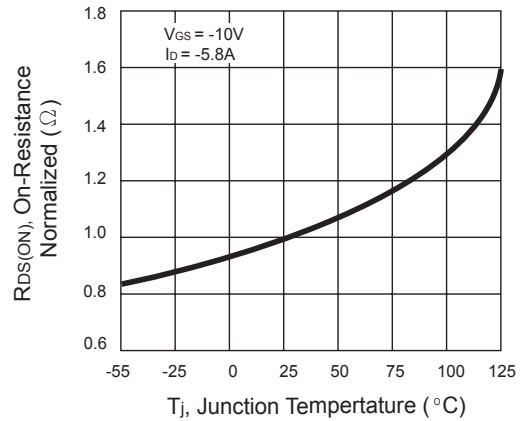


Figure 4. On-Resistance Variation with Temperature

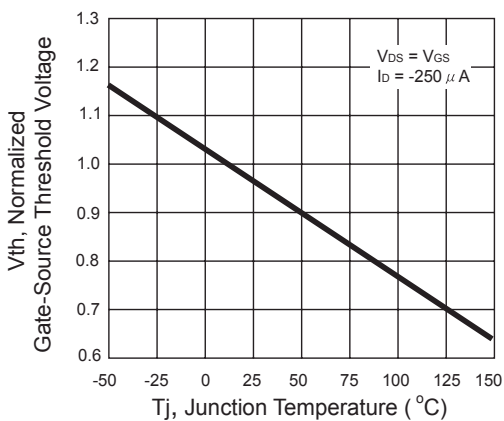


Figure 5. Gate Threshold Variation with Temperature

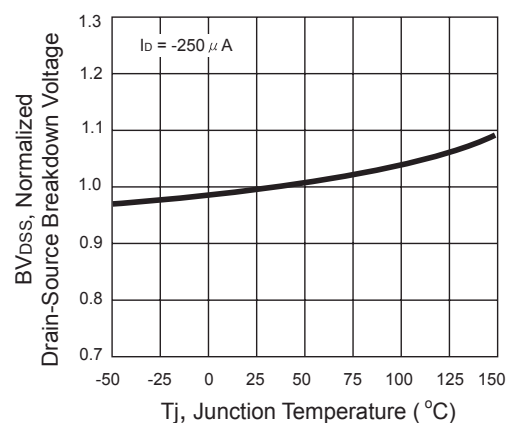


Figure 6. Breakdown Voltage Variation with Temperature

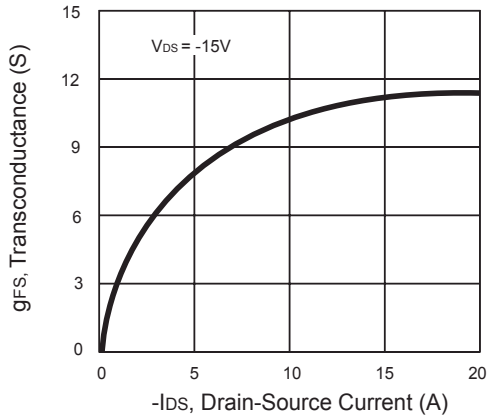


Figure 7. Transconductance Variation with Drain Current

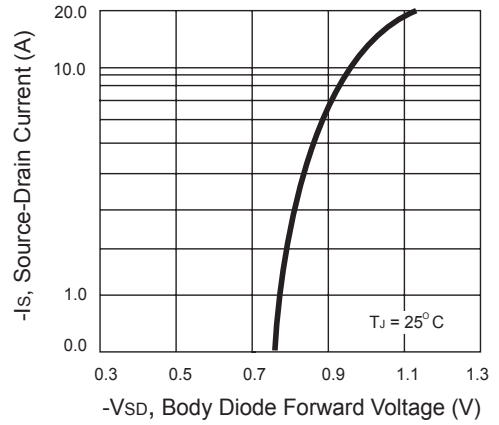


Figure 8. Body Diode Forward Voltage Variation with Source Current

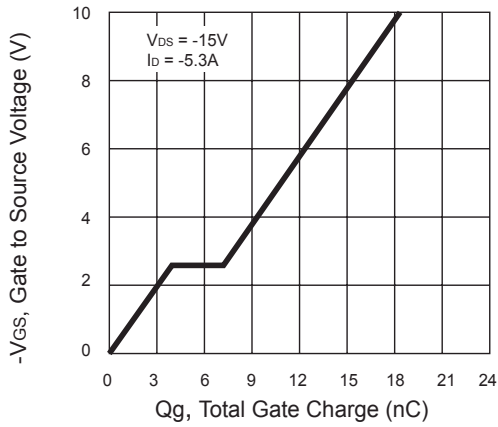


Figure 9. Gate Charge

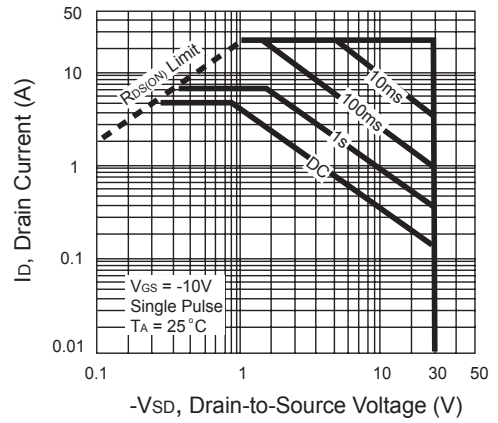


Figure 10. Maximum Safe Operating Area

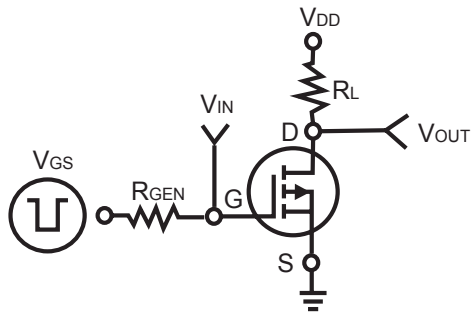


Figure 11. Switching Test Circuit

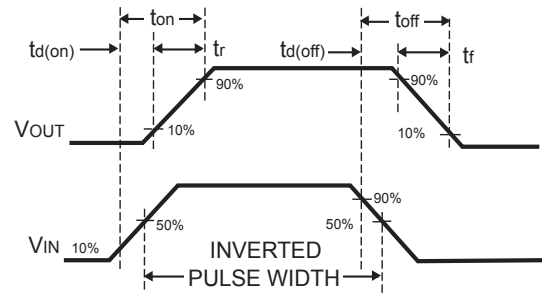


Figure 12. Switching Waveforms

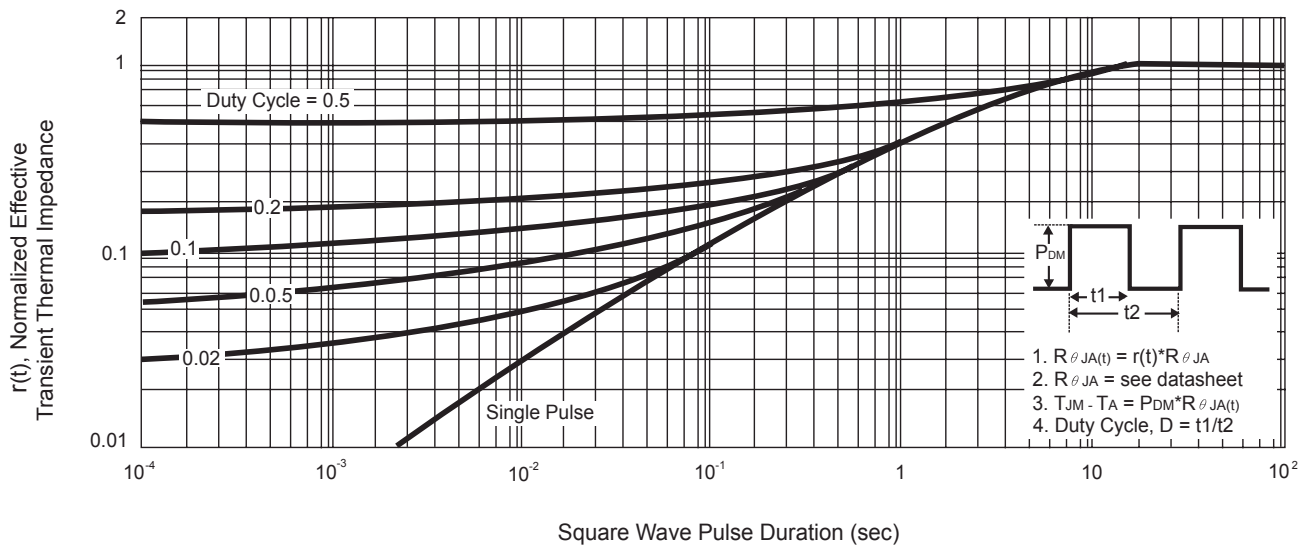
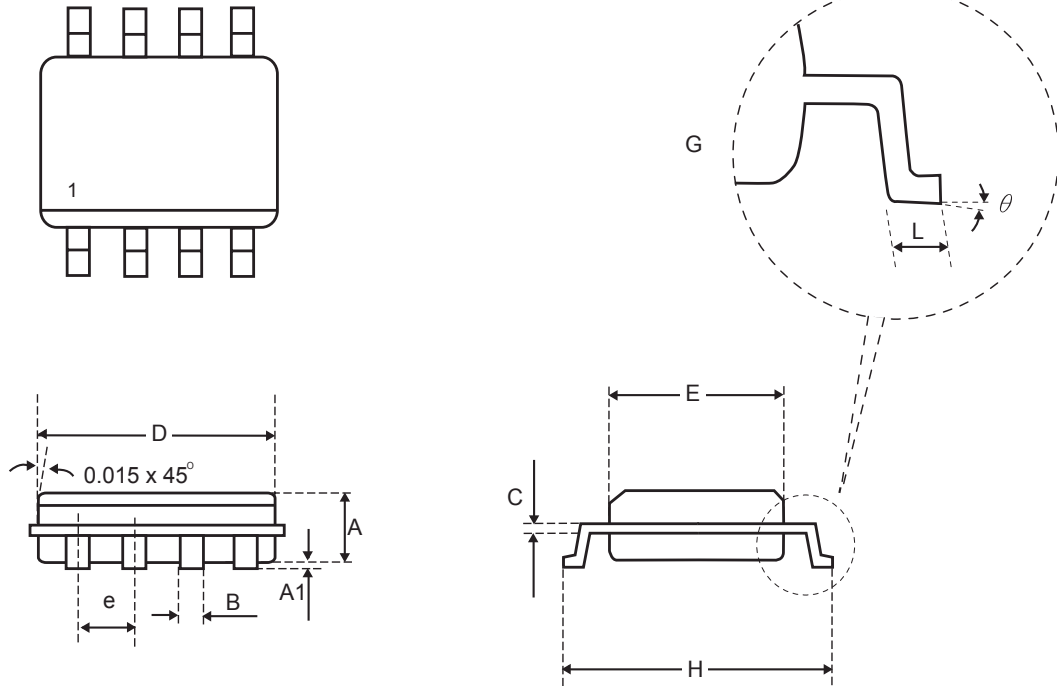


Figure 13. Normalized Thermal Transient Impedance Curve



Package Outline Dimensions

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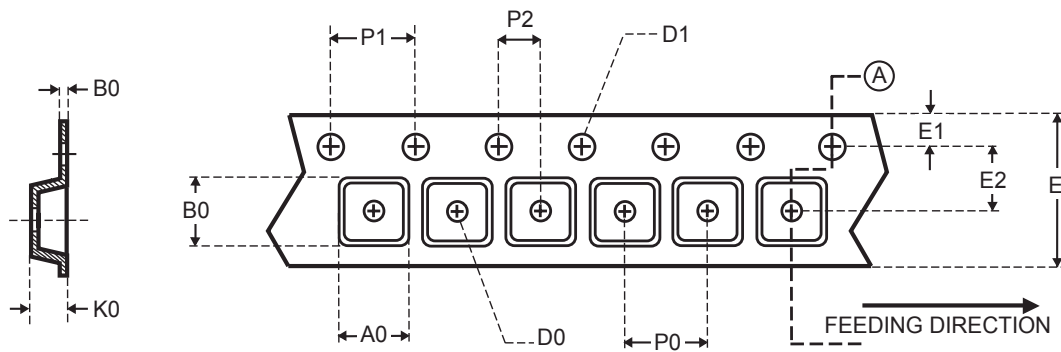


| SYMBOLS | MILLIMETERS | | INCHES | |
|----------|-------------|------|------------|-------|
| | Min. | Max. | Min. | Max. |
| A | 1.35 | 1.75 | 0.053 | 0.069 |
| A1 | 0.10 | 0.25 | 0.004 | 0.010 |
| B | 0.41 Typ. | | 0.016 Typ. | |
| C | 0.20 Typ. | | 0.008 Typ. | |
| D | 4.80 | 4.98 | 0.189 | 0.196 |
| E | 3.81 | 3.99 | 0.150 | 0.157 |
| e | 1.25 Typ. | | 0.05 Typ. | |
| H | 5.79 | 6.20 | 0.228 | 0.244 |
| L | 0.41 | 1.27 | 0.016 | 0.050 |
| θ | 0° | 8° | 0° | 8° |



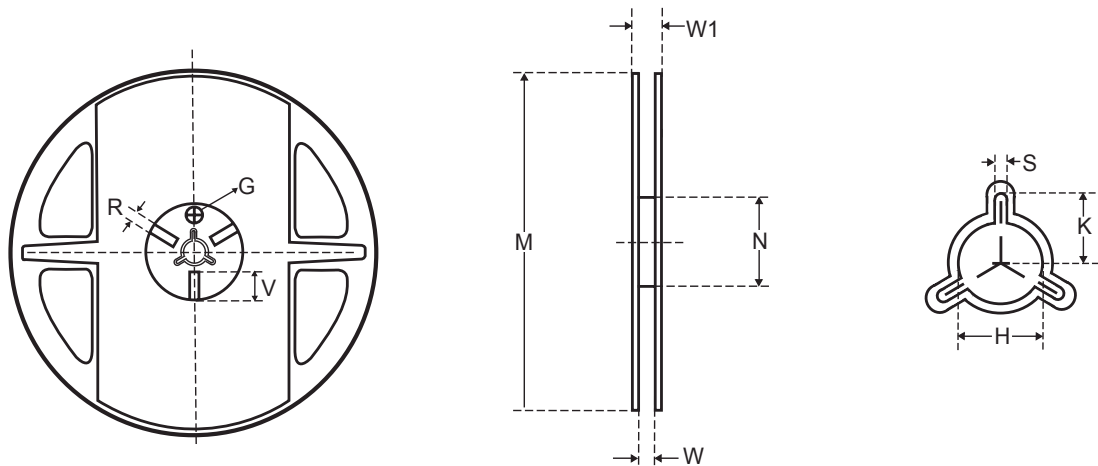
Carrier Tape & Reel Dimensions

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| Package | A0 | B0 | K0 | D0 | D1 | E | E1 | E2 | P0 | P1 | P2 | T |
|-------------------|------|------|------|-----------------------|-------------------------------|---------------------|------|--------------------|------|------|--------------------|--------------------|
| SOP 8N 150 mil | 6.40 | 5.20 | 2.10 | $\psi 1.50$ (Min.) | $\psi 1.50$ +0.10 -0.10 | 12.00 ± 0.30 | 1.75 | 5.50 ± 0.05 | 8.00 | 4.00 | 2.00 ± 0.05 | 0.30 ± 0.05 |

UNIT : mm



| Tape size | Reel Size | M | N | W | W1 | H | K | S | G | R | V |
|-----------|------------|----------------|-----------------|-------------------|--------------|----------------------------|---|-------------------|---|---|---|
| 12mm | $\psi 330$ | 330 ± 1 | 62 ± 1.5 | 12.4 ± 0.2 | 16.8 -0.4 | $\psi 12.75$ ± 0.15 | - | 2.0 ± 0.15 | - | - | - |

UNIT : mm